FFSH4065ADN-F155

Silicon Carbide Schottky Diode

650 V, 40 A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 95 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- This Device is Pb−Free and is RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

ON Semiconductor®

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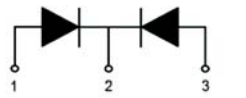
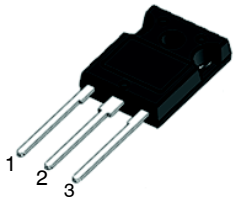
V_{RRM}	I_F
650 V	40 A



1. Anode 2. Cathode/ Case 3. Anode



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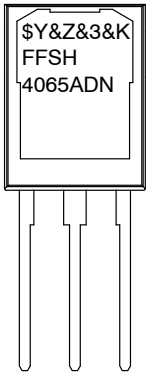
CASE 340CH

MARKING DIAGRAM



$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FFSH4065ADN	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSH4065ADN−F155	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
E_{AS}	Single Pulse Avalanche Energy (Note 1)		95	mJ
I_F	Continuous Rectified Forward Current	@Tc < 140°C	20* / 40**	A
	Continuous Rectified Forward Current	@ Tc < 135°C	22* / 44**	
$I_{F, Max}$	Non−Repetitive Peak Forward Surge Current	Tc = 25°C, 10 μs	1100	A
		Tc = 150°C, 10 μs	1000	A
$I_{F, SM}$	Non−Repetitive Forward Surge Current		105	A
$I_{F, RM}$	Repetitive Forward Surge Current		58	A
P_{tot}	Power Dissipation	Tc = 25°C	150	W
		Tc = 150°C	25	W
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +175	°C
	TO247 Mounting Torque, M3 Screw		60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
*Per leg.
**Per Device.
1. E_{AS} of 95 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 19.5 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.0* / 0.5**	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH4065ADN−F155	FFSH4065ADN	TO-247 Long Lead	Tube	N/A	N/A	30 Units

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_F	Forward Voltage	IF = 20 A, Tc = 25°C	–	1.5	1.75	V
		IF = 20 A, Tc = 125°C	–	1.6	2.0	
		IF = 20 A, Tc = 175°C	–	1.72	2.4	
I_R	Reverse Current	VR = 650 V, Tc = 25°C	–	–	200	μA
		VR = 650 V, Tc = 125°C	–	–	400	
		VR = 650 V, Tc = 175°C	–	–	600	
Q_C	Total Capacitance Charge	V = 400 V	–	64	–	nC
C	Total Capacitance	VR = 1 V, f = 100 kHz	–	1085	–	pF
		VR = 200 V, f = 100 kHz	–	117	–	
		VR = 400 V, f = 100 kHz	–	88	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

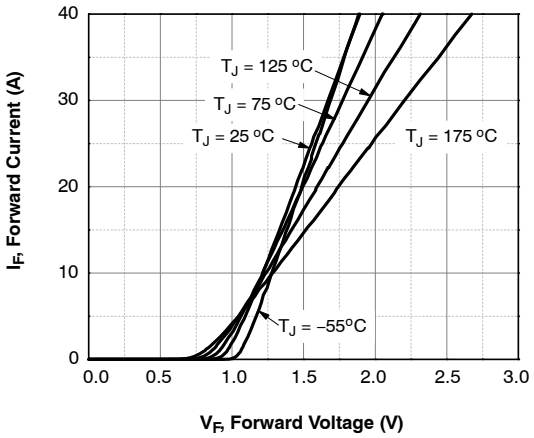


Figure 1. Forward Characteristics

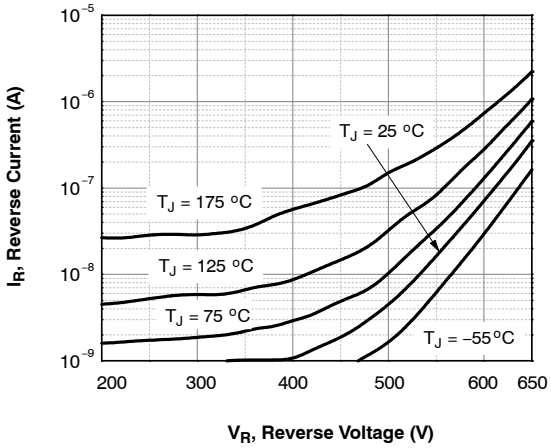


Figure 2. Reverse Characteristics

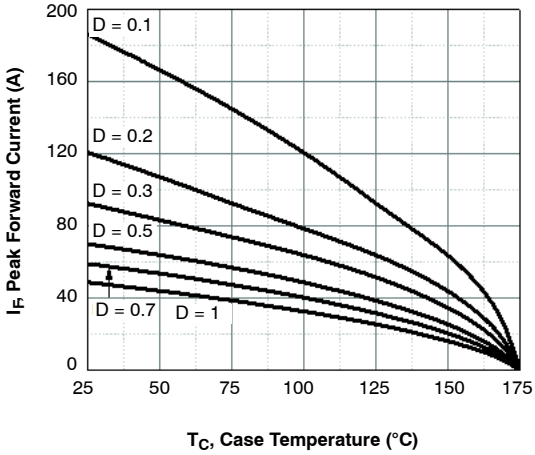


Figure 3. Current Derating

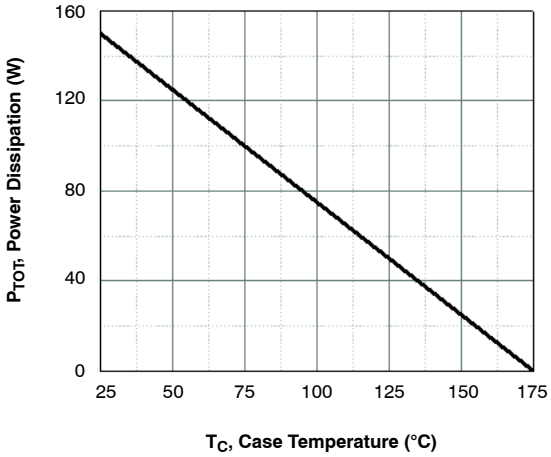


Figure 4. Power Derating

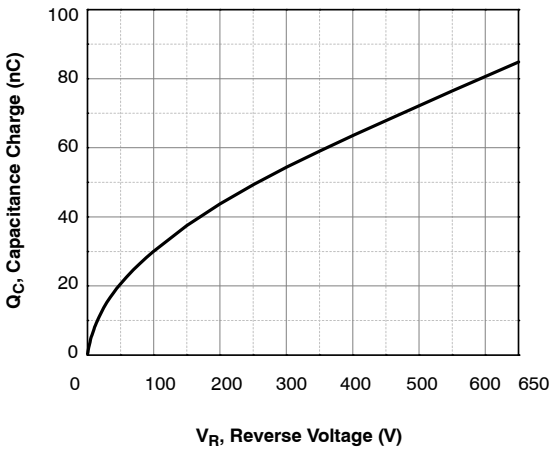


Figure 5. Capacitive Charge vs. Reverse Voltage

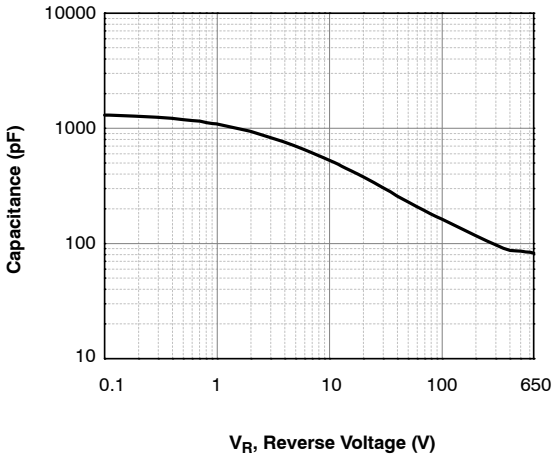


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS (Continued)

(T_J = 25°C unless otherwise noted)

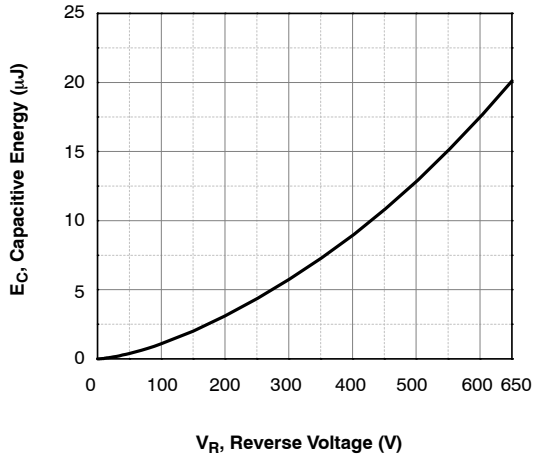


Figure 7. Capacitance Stored Energy

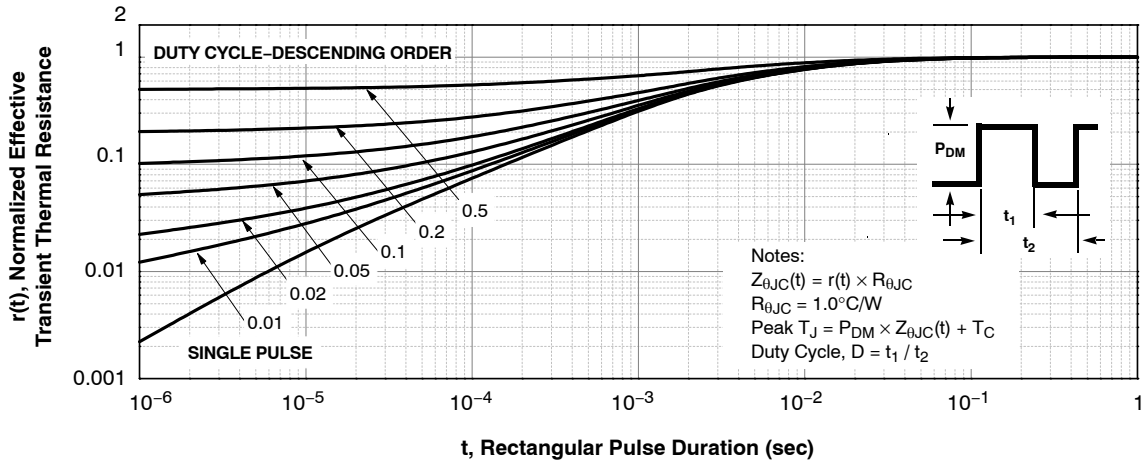


Figure 8. Junction−to−Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

L = 0.5 mH
R < 0.1 Ω
V_{DD} = 50 V
EAVL = 1/2LI2 [$V_{R(AVL)}$/($V_{R(AVL)}$ − V_{DD})]
Q1 = IGBT (BV_{CES} > DUT $V_{R(AVL)}$)

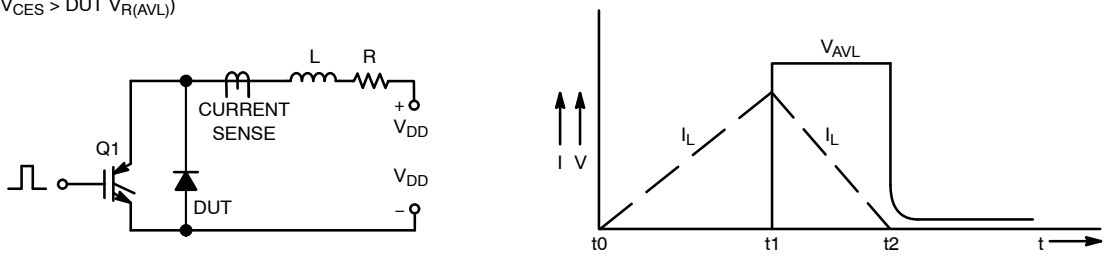


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

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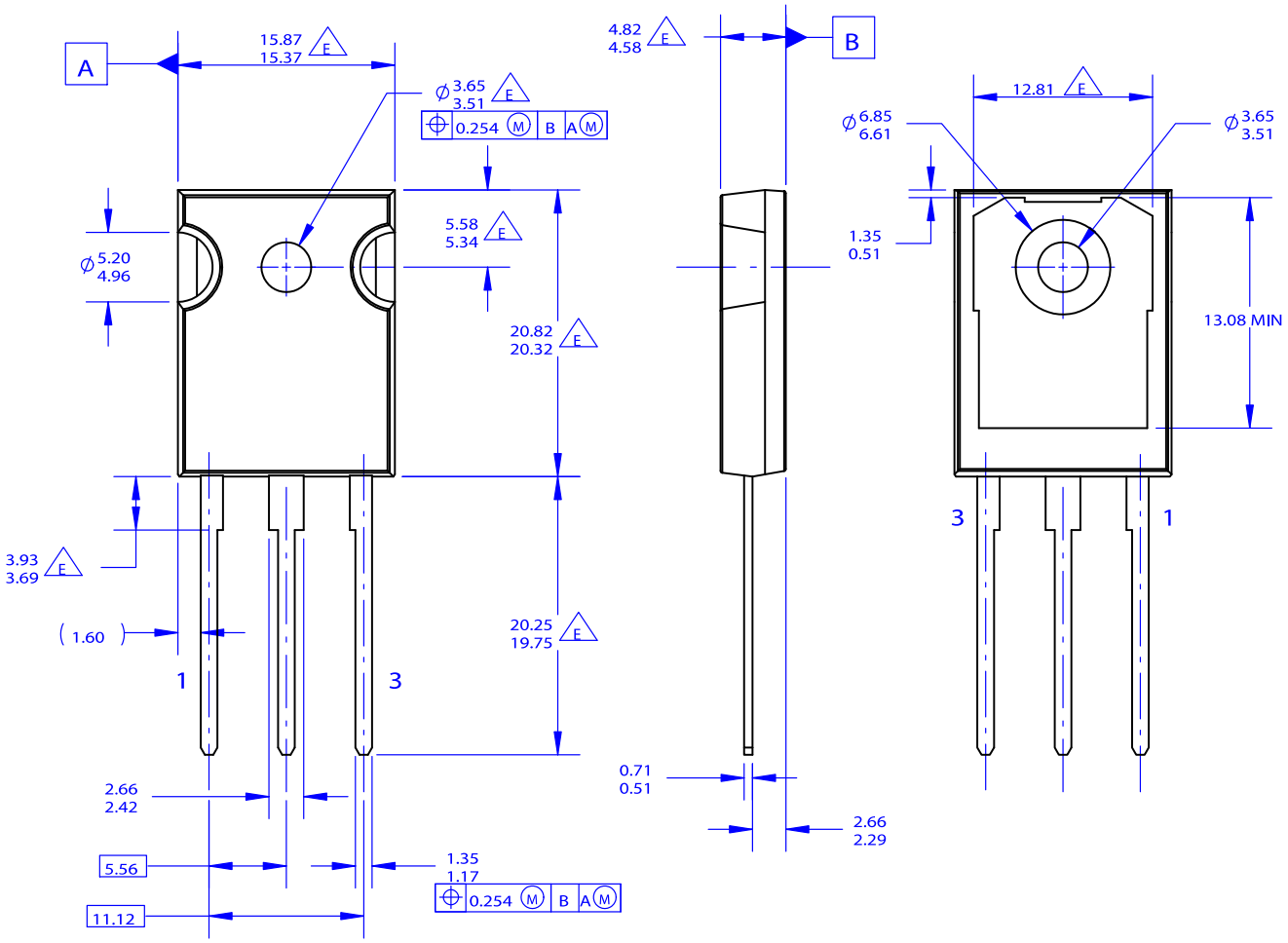

NOTES: UNLESS OTHERWISE SPECIFIED.

A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DRAWING CONFORMS TO ASME Y14.5 - 1994

E DOES NOT COMPLY JEDEC STANDARD VALUE

ISSUE	REVISION	DATE
O	RELEASED FOR PRODUCTION FROM FAIRCHILD TO247G03 TO ON SEMICONDUCTOR. REQ. BY J. LETTERMAN.	31 OCT 2016

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
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